



SWTEST

PROBE TODAY, FOR TOMORROW

2023 CONFERENCE

Challenges and Innovations in Developing High-Density, Low-Power DPS Solutions for 5nm and Smaller Process Geometries in ATE

ELEVATE
SEMICONDUCTOR

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Overview

- Demand is Driving Smaller Process Nodes
- Challenges of $\leq 5\text{nm}$ Process Nodes on DPS Solutions
 - Fast Load Transient Response
 - High DC Accuracy
 - High Power Efficiency
- Introduction to Elevate Semiconductor
- Future ATE Solutions
- Collaboration

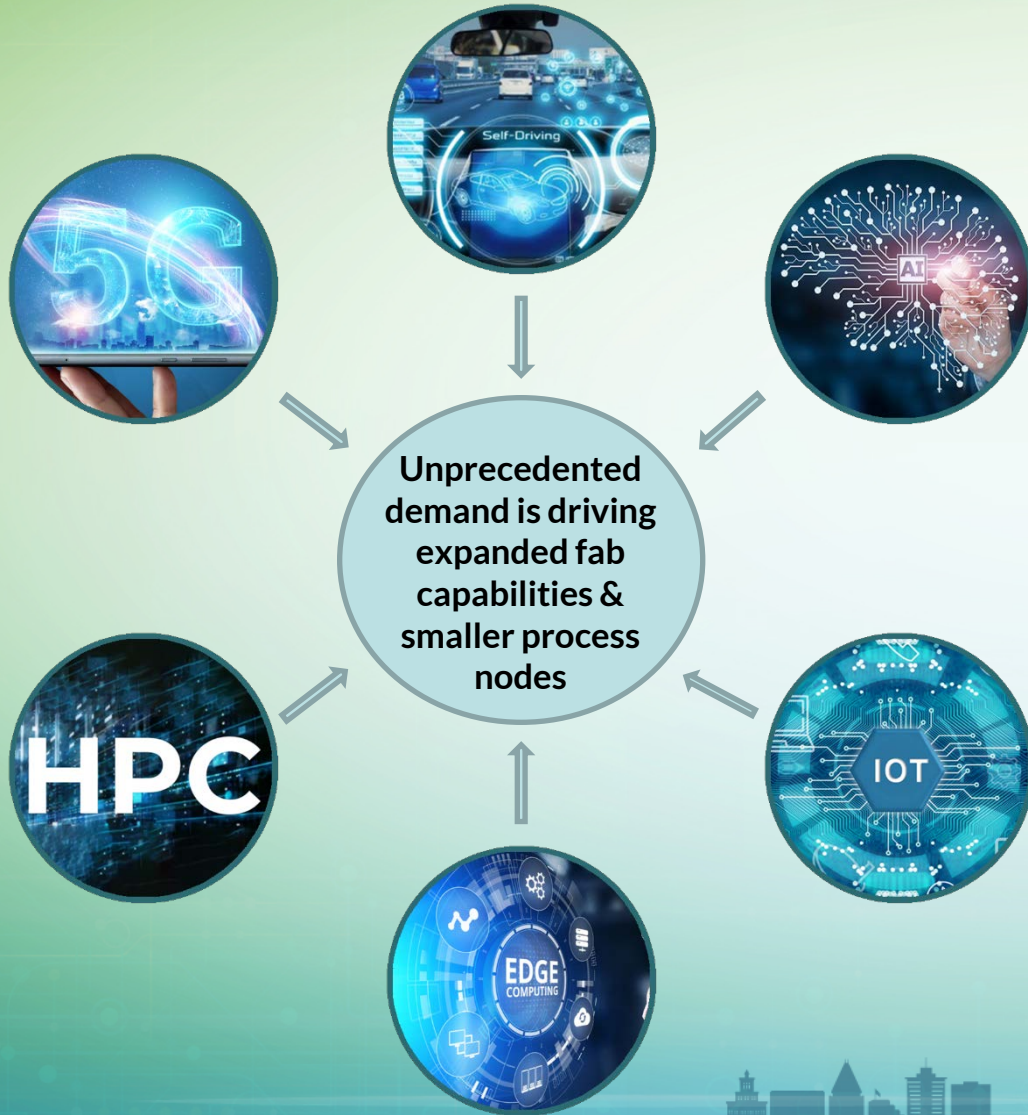
Demand is Driving Smaller Process Nodes

\$150B+ in Fabs Under Development

Foundry	Node	Investment	Completion	Location
Global Foundries	14nm	\$1B	2023	New York
Intel	7nm	\$10B	2023	Israel
	2nm	\$20B	2024	Arizona
	2nm		2024	
	2nm	\$28B	2025	Ohio
2nm	2025			
Samsung	3nm	\$17B	2024	Texas
	3nm	?	2022	Korea
	3nm	?	2020	
	2nm	?	2025	
TSMC	7nm	\$10B	2024	Taiwan
	5nm	\$12B	2024	Arizona
	3nm	\$20B	2023	Taiwan
	2nm	?	2025	
	1.4nm	?	2027	
Texas Instruments	45-130nm	\$30B	2025	Texas

- Intel: \$100B in Europe; \$80B in Ohio
- Micron: \$100B in New York

Source: The Information Network and Tom's Hardware



Challenges of $\leq 5\text{nm}$ Process Nodes

Along with smaller geometries come:

- Reduced operating voltage ($< 1\text{V}$)
- Larger current consumption (100s or 1,000s of amps)
- Higher speeds (multiple Gbps)
- Higher pin counts (1,000s of pins)

How does this affect probe card design?

- Higher pin counts require tighter pitch and smaller pad sizes
- High-density interconnects require similarly high-density associated electronics
- Large currents cause excess heat, probe damage

Requirements for Device Power Supplies

- Fast Load Transient Response (enables fast scans)
- High DC Accuracy (increases yield, quality)
- Improved Power Efficiency (allows greater density)



Apple A17, TSMC 3nm
(Iphone 15 Pro/Ultra)

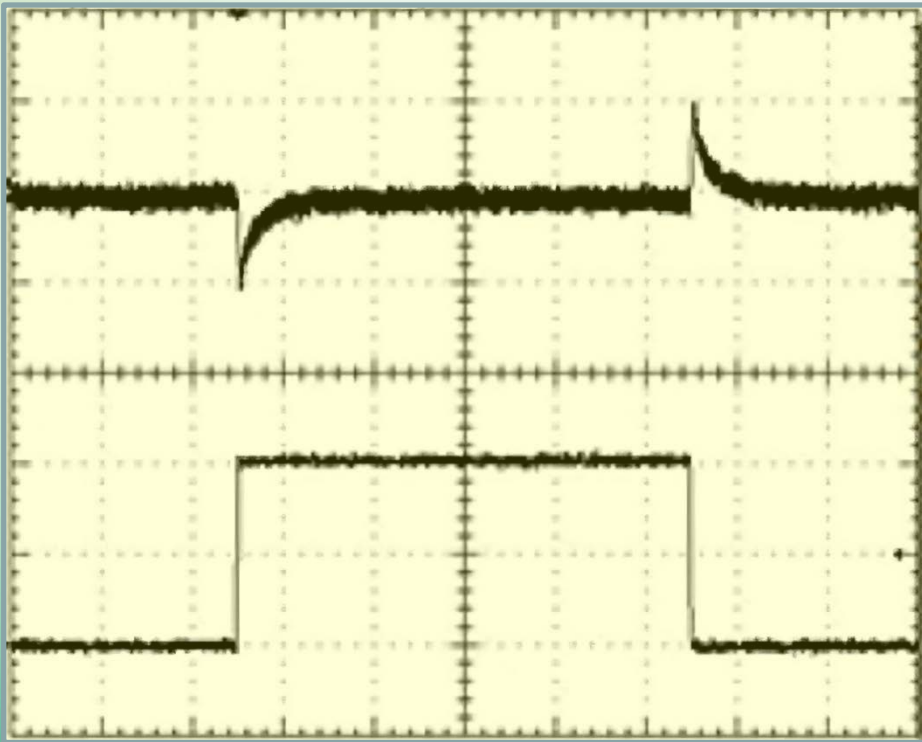


Nvidia H100 GPU/AI, TSMC 4nm

Challenges of $\leq 5\text{nm}$ Process Nodes

DPS: Fast Load Transient Response

Vout



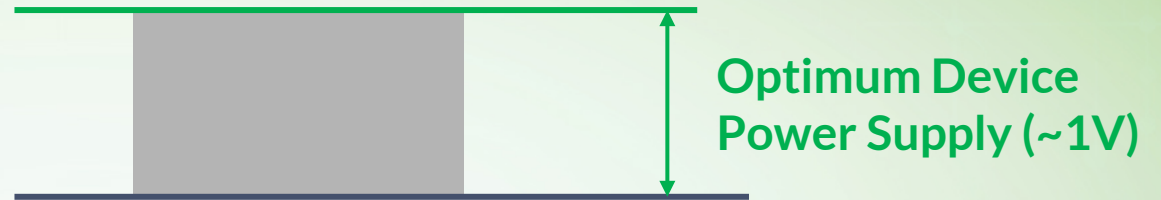
Iout

- As scan patterns begin, large current causes Vdroop
- If too large, can reset DUT and cause a false failure
- Running scans at a slower speed or staggering starts can mitigate droop, but this will increase test time and COT

Challenges of $\leq 5\text{nm}$ Process Nodes

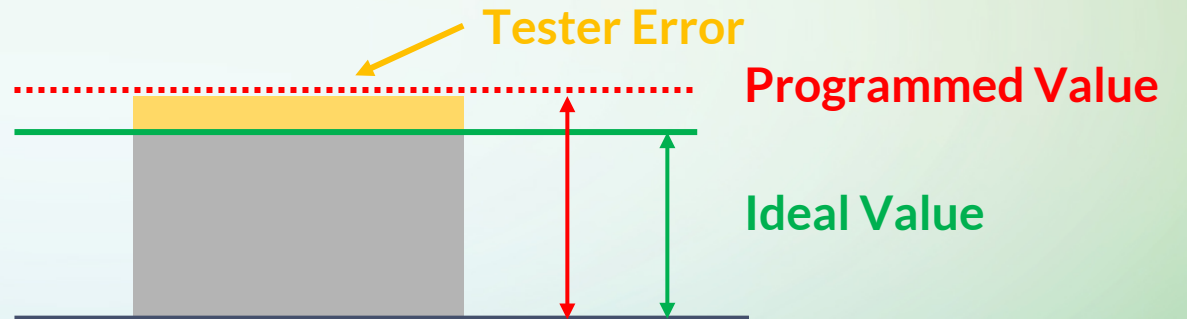
DPS: High DC Accuracy (millivolts or less)

Ideal tester has perfect accuracy



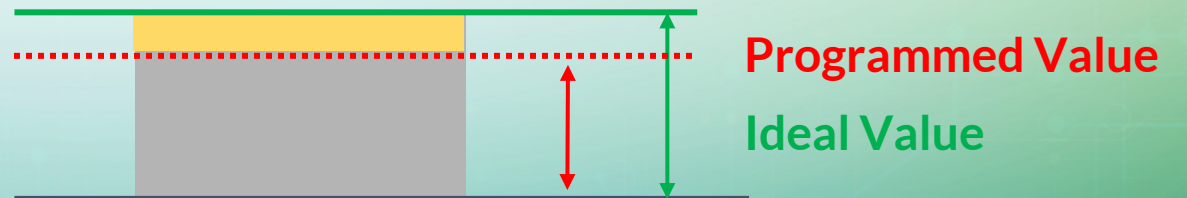
Programmed to higher value to ensure yield

- Wastes power
- DUT runs hotter
- Might need to run slower scans



Programmed to lower value to ensure quality

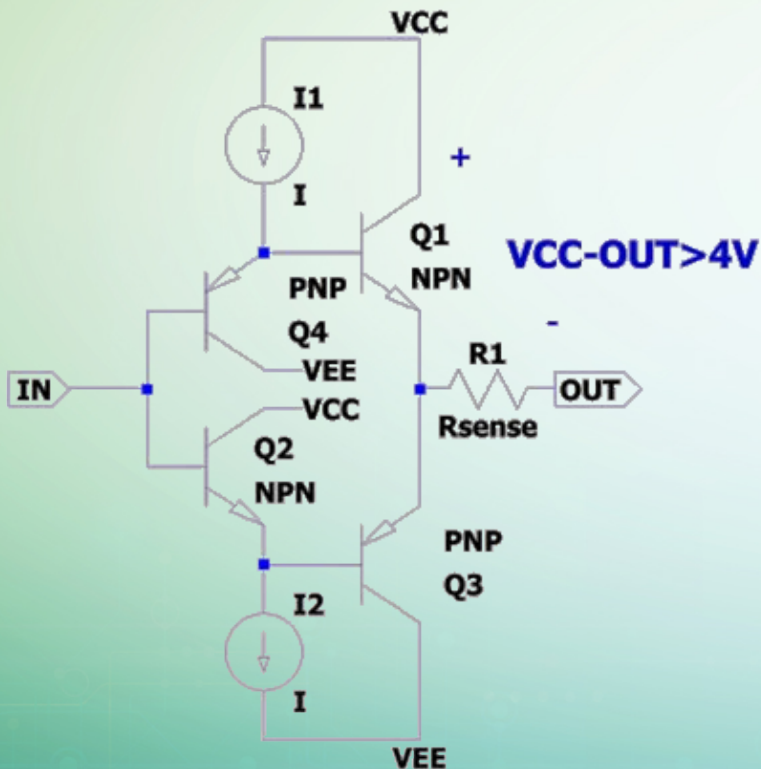
- May reduce yield



Challenges of $\leq 5\text{nm}$ Process Nodes

DPS: High Power Efficiency

Common Linear Solution



- This architecture requires large headroom:
for $V_{out} = 1\text{V}$, V_{cc} must be $\geq 5\text{V}$

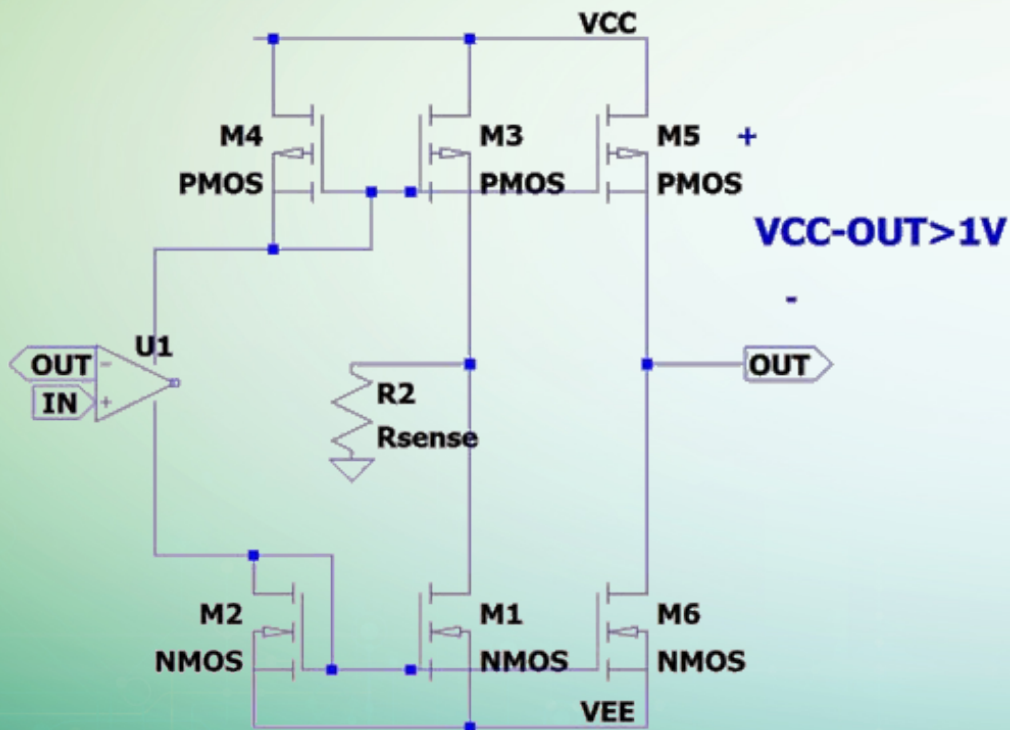
- Poor Efficiency = $\frac{P_{out}}{P_{in}} = \frac{I * V_{out}}{I * V_{in}} = \frac{1\text{V}}{5\text{V}} = 20\%$

- For every 1W delivered to the load, 4W are wasted

Challenges of $\leq 5\text{nm}$ Process Nodes

DPS: High Power Efficiency

Elevate's Linear Solution



- This architecture allows smaller headroom:
for $V_{out} = 1V$, V_{cc} must be $\geq 2V$

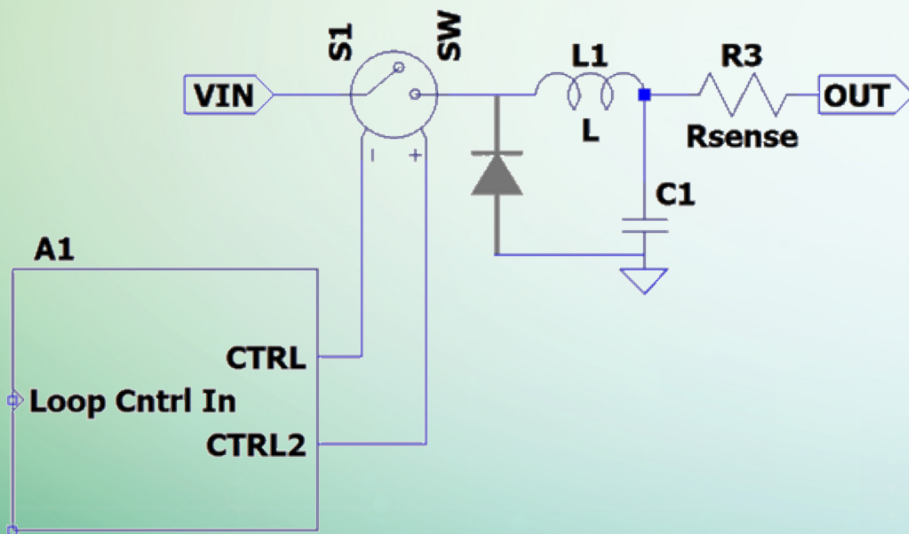
- Improved Efficiency = $\frac{P_{out}}{P_{in}} = \frac{I * V_{out}}{I * V_{in}} = \frac{1V}{2V} = 50\%$

- For every 1W delivered to the load, only 1W is wasted

Challenges of $\leq 5\text{nm}$ Process Nodes

DPS: High Power Efficiency

Elevate's Next-Gen Switch-Mode DPS



- Linear supplies are only power efficient when V_{cc} is optimized for V_{out}
- Switch-mode power supplies are efficient across a wide voltage range

$$\text{Power Efficiency} = \frac{P_{out}}{P_{in}} = \frac{P_{out}}{P_{out} + P_D} = 75-90\%$$

$$\text{where } P_D = P_L + P_{Conduction} + P_{Switching}$$

- For every 1W delivered to the load, only 250mW is wasted (80% efficient)

Elevate Semiconductor History and Product Focus

The only major IC supplier whose sole focus is test



Wafer Probe & Package Test

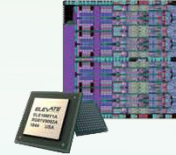


Instrumentation

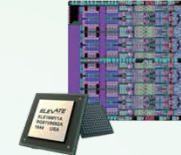
PE



Venus Family



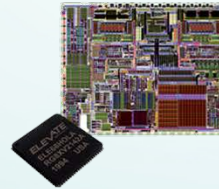
Custom PE & TG



Mystery

- ➔ First fully-integrated PE with DCL, DACs, PMUs & Deskews
- ➔ Product line has evolved to improve speed, density & power efficiency

DPS



Jupiter



Vesuvius



Custom

- ➔ First fully-integrated DPS with internal DACs
- ➔ Latest products have higher channel count, higher power efficiency & smaller footprint

VI



Pluto



Triton



Saturn (hybrid)

- ➔ First fully-integrated octal VI with internal comparators & DACs
- ➔ Latest products have increased output voltages

Elevate's New Solutions: DPS/PMU

Kilauea

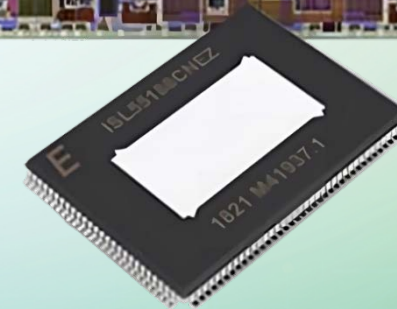
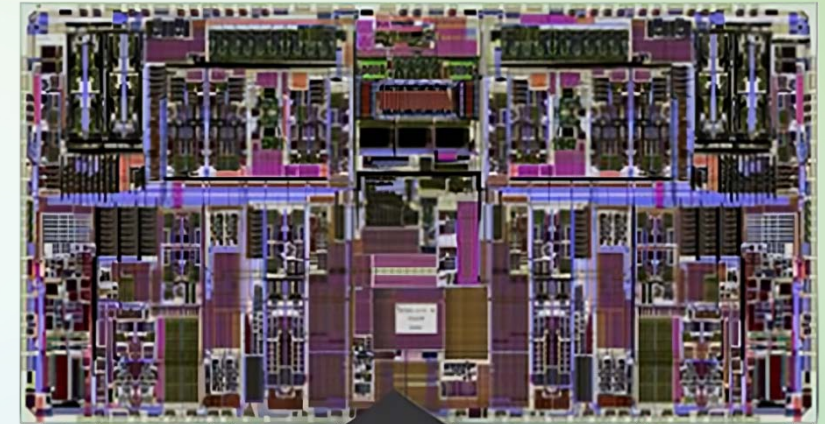
- Improved architecture, high efficiency quad DPS (34V/5A)
- 4 auto-selectable supplies to minimize headroom
- 100uV accuracy (target)
- Internal ganging up to 20A

Shuksan

- Switch-mode architecture DPS for max efficiency (75%)
- Chiplet add-on to provide envelope tracking for Kilauea
- High-density quad, 34V

Whitney

- Highest voltage dual fully-integrated DPS/PMU (+/- 64V)
- Integrated DACs, MI, monitors
- Applications in Automotive, PoE, PMIC Quick Charge, LED drivers



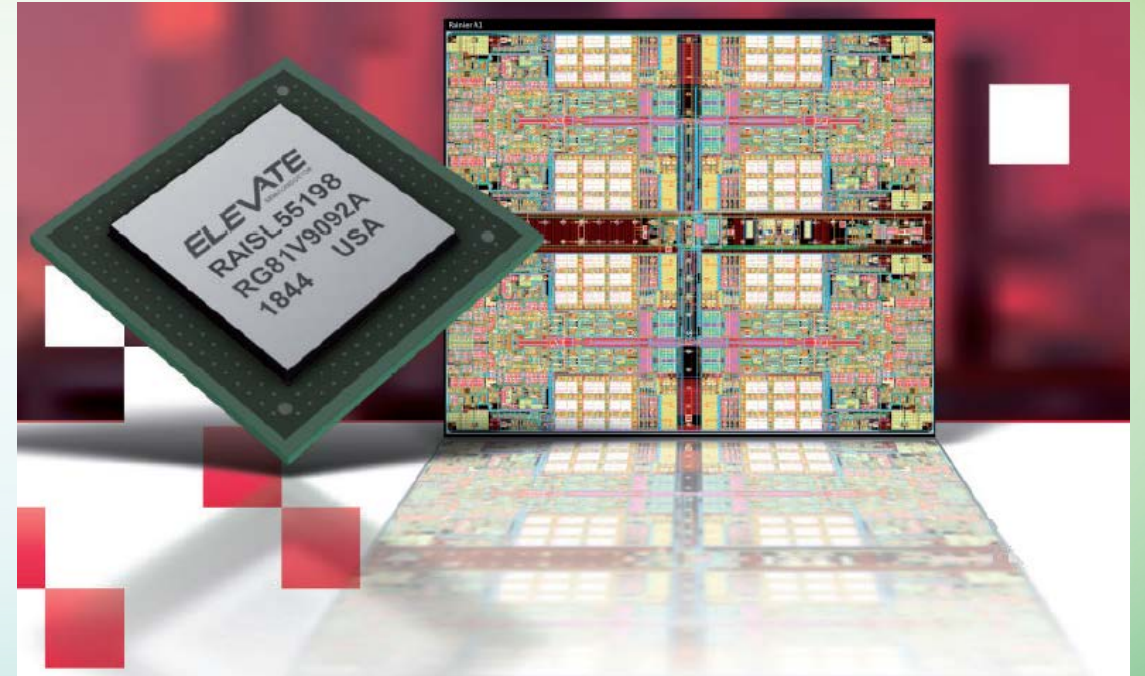
Elevate's New Solutions: Pin Electronics

Rainier

- Lowest power, fully-integrated 2Gbps octal PE
- High-density design includes integrated PPMU/DAC/Deskew/Load
- < 500mW/channel

Longs Peak

- Octal 7.5Gbps PE
- < 1W/channel (target)
- Integrated timing generation

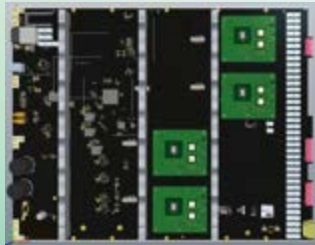


Collaboration

Instruments



HD VI based on Jupiter



IO core based on Mystery
DPIN16 module, PXI: 32/64



HD PMU based on Neptune

Custom & Semi-Custom Engagements

We are flexible and value customer input as we develop solutions together





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Thank You

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